



Product data sheet

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ESD5V0U1BL-MS HF

Semiconductor

Compiance

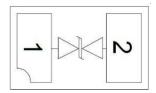
Features

30W (8/20µs) Peak Pulse Power Low Capacitance ESD Protection SOD-882 Package RoHS Compliant Matte Tin Lead finish (Pb-Free) Protect One High Speed Data Line Meet IEC61000-4-2 Level 4: Contact Discharge > 8kV Air Discharge > 15kV

Applications

Communication System Portable Instrumentation Audio and Video Equipment Computers and Peripherals USB 1.1, USB 2.0 Ports





DFN1006

Symbol	Parameter	Value	Unit
Ррк	Peak Pulse Power	30	W
IPP	Peak Pulse Current	2	А
VESD (Contact)	Contact ESD Voltage per IEC61000-4-2	8	kV
VESD (Air)	Air ESD Voltage per IEC61000-4-2	15	kV
TJ	Junction Temperature	-55 to +150	Ĉ
TSTG	Storage Temperature	-55 to +150	Ĉ

Electrical Characteristics (Ta = 25℃)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VRWM	Reverse Working Peak Voltage				5	V
VBR	Reverse Breakdown Voltage	IT = 1mA	5.5		9.5	V
IR	Reverse Leakage Current	VRWM = 5V			0.1	μA
VC	Clamping Voltage	IPP = 1A (8/20µs)			12	V
VC	Clamping Voltage	IPP = 2A (8/20µs)			15	V
CJ	Capacitance	VR = 0V, f = 1MHz		3.0	3.5	рF

Maximum Ratings (Ta = 25℃)





Electrical Parameter

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ IPP
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
Ι _Τ	Test Current
V _{BR}	Breakdown Voltage @ I⊤

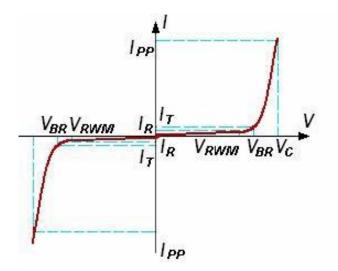
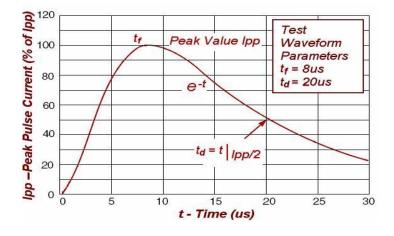
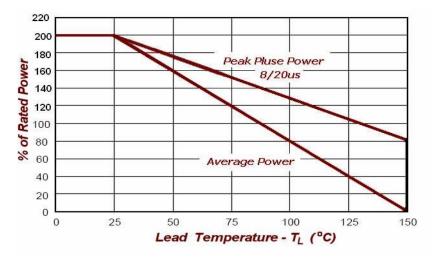


FIG1: Pulse Waveform



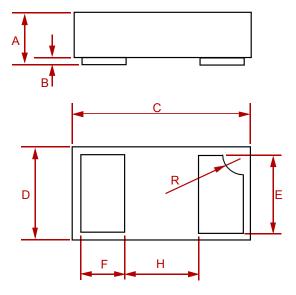






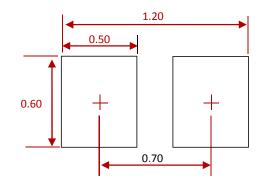
ESD5V0U1BL-MS

PACKAGE MECHANICAL DATA



Dim	Inches		Millimeters	
	MIN	MAX	MIN	МАХ
A	0.0125	0.02	0.32	0.52
В	0.000	0.002	0.00	0.05
С	0.037	0.043	0.95	1.080
D	0.022	0.027	0.55	0.680
E	0.016	0.024	0.40	0.60
F	0.008	0.012	0.20	0.30
н	0.015Typ.		0.40Typ.	
R	0.001	0.005	0.05	0.15

Suggested Pad Layout



NOTES:

- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

REEL SPECIFICATION

P/N	PKG	QTY
ESD5V0U1BL-MS	DFN1006	10000





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